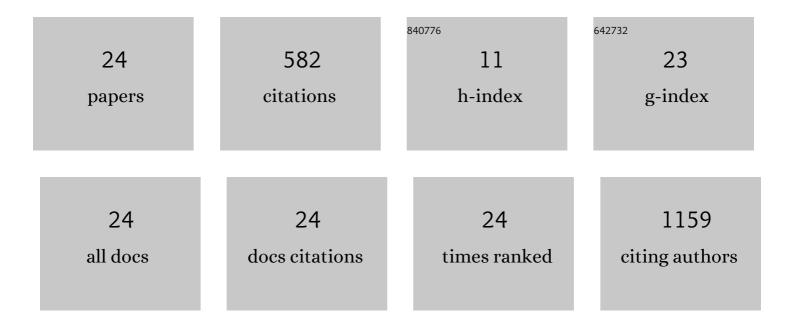
Subir Parui

List of Publications by Year in descending order

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#	Article	IF	CITATIONS
1	A molecular spin-photovoltaic device. Science, 2017, 357, 677-680.	12.6	147
2	Gate-tunable diode and photovoltaic effect in an organic–2D layered material p–n junction. Nanoscale, 2015, 7, 15442-15449.	5.6	84
3	Gateâ€Controlled Energy Barrier at a Graphene/Molecular Semiconductor Junction. Advanced Functional Materials, 2015, 25, 2972-2979.	14.9	58
4	Temperature dependent transport characteristics of graphene/n-Si diodes. Journal of Applied Physics, 2014, 116, .	2.5	53
5	Energy Level Alignment at Metal/Solutionâ€Processed Organic Semiconductor Interfaces. Advanced Materials, 2017, 29, 1606901.	21.0	37
6	Spin doping using transition metal phthalocyanine molecules. Nature Communications, 2016, 7, 13751.	12.8	30
7	Graphene as an electrode for solution-processed electron-transporting organic transistors. Nanoscale, 2017, 9, 10178-10185.	5.6	30
8	Probing electron transport across a LSMO/Nb:STO heterointerface at the nanoscale. Physical Review B, 2013, 87, .	3.2	17
9	Hot electron transport in a strongly correlated transition-metal oxide. Scientific Reports, 2013, 3, 1274.	3.3	16
10	Hot Electrons and Hot Spins at Metal–Organic Interfaces. Advanced Functional Materials, 2018, 28, 1706105.	14.9	12
11	Robust Spin Interconnect with Isotropic Spin Dynamics in Chemical Vapor Deposited Graphene Layers and Boundaries. ACS Nano, 2020, 14, 15864-15873.	14.6	12
12	Nanoscale hot electron transport across Cu/nâ€&i(100) and Cu/nâ€&i(111) interfaces. Physica Status Solidi - Rapid Research Letters, 2011, 5, 388-390.	2.4	10
13	Hot electron transmission in metals using epitaxial NiSi2/n-Si(111) interfaces. Applied Physics Letters, 2011, 99, 032104.	3.3	10
14	Frequency driven inversion of tunnel magnetoimpedance and observation of positive tunnel magnetocapacitance in magnetic tunnel junctions. Applied Physics Letters, 2016, 109, 052401.	3.3	10
15	Probing hot electron transport across an epitaxial Schottky interface of SrRuO3/Nb:SrTiO3. Applied Physics Letters, 2013, 102, .	3.3	8
16	Reliable determination of the Cu/n-Si Schottky barrier height by using in-device hot-electron spectroscopy. Applied Physics Letters, 2015, 107, .	3.3	8
17	Strain Effects on the Energy-Level Alignment at Metal/Organic Semiconductor Interfaces. ACS Applied Materials & Interfaces, 2019, 11, 12717-12722.	8.0	8
18	Comparison of hot-electron transmission in ferromagnetic Ni on epitaxial and polycrystalline Schottky interfaces. Physical Review B, 2012, 85, .	3.2	7

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#	Article	IF	CITATIONS
19	Gate-tunable graphene-organic interface barrier for vertical transistor and logic inverter. Applied Physics Letters, 2018, 113, .	3.3	7
20	Molecular spectroscopy in a solid-state device. Materials Horizons, 2019, 6, 1663-1668.	12.2	7
21	Top dielectric induced ambipolarity in an n-channel dual-gated organic field effect transistor. Journal of Materials Chemistry C, 2019, 7, 10389-10393.	5.5	5
22	Hot electron attenuation of direct and scattered carriers across an epitaxial Schottky interface. Journal of Physics Condensed Matter, 2013, 25, 445005.	1.8	3
23	Evidence of spin scattering and collection of hot electrons at different conduction minima in Si. Applied Physics Letters, 2013, 103, 082409.	3.3	2
24	Spin transport in metal and oxide devices at the nanoscale. , 2012, , .		1